

For Muting (20V, 0.3A)

2SD2704K / 2SD2705S

●Features

- 1) High DC current gain.
h_{FE} = 820 to 2700
- 2) High emitter-base voltage.
V_{EB0} = 25V (Min.)
- 3) Low Ron
Ron = 0.7Ω (Typ.)

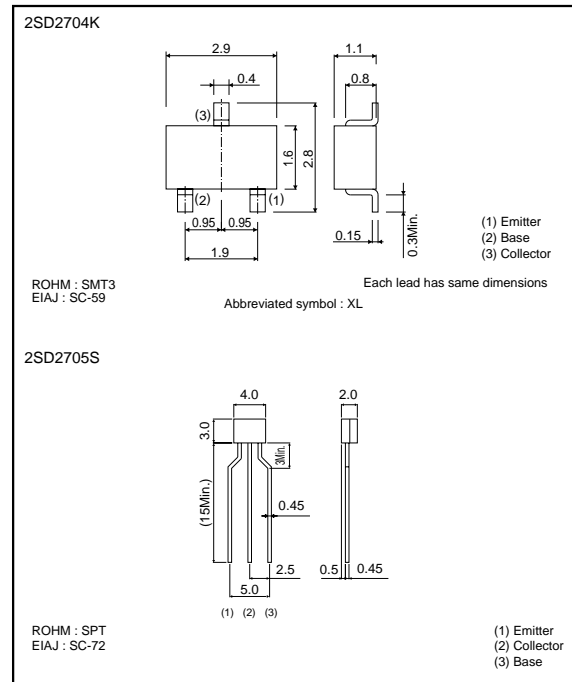
●Structure

Epitaxial planar type
NPN silicon transistor

●Packaging specifications

Type	Package	Taping	
	Code	T146	TP
	Basic ordering unit (pieces)	3000	5000
2SD2704K		○	-
2SD2705S		-	○

●External dimensions (Unit : mm)



●Absolute maximum ratings (T_a=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CE0}	20	V
Emitter-base voltage	V _{EB0}	25	V
Collector current	I _c	0.3	A
Collector power dissipation	2SD2704K	0.2	W
	2SD2705S	0.3	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	50	–	–	V	I _C =10μA
Collector-emitter breakdown voltage	BV _{CEO}	20	–	–	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EB0}	25	–	–	V	I _E =10μA
Collector cutoff current	I _{CB0}	–	–	0.1	μA	V _{CB} =50V
Emitter cutoff current	I _{EB0}	–	–	0.1	μA	V _{EB} =25V
Collector-emitter saturation voltage	V _{CE(sat)}	–	50	100	mV	I _C /I _B =30mA/3mA
DC current transfer ratio	h _{FE}	820	–	2700	–	V _{CE} =2V, I _C =4mA
Transition frequency	f _T *	–	35	–	MHz	V _{CE} =6V, I _E =-4mA, f=10MHz
Output capacitance	C _{ob}	–	3.9	–	pF	V _{CB} =10V, I _E =0A, f=1MHz
Output On-resistance	R _{on}	–	0.7	–	Ω	I _B =5mA, V _i =100mV(rms), f=1kHz

* Measured using pulse current

●Electrical characteristic curves

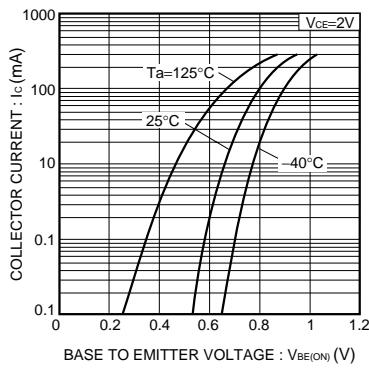


Fig.1 Grounded emitter propagation characteristics (I)

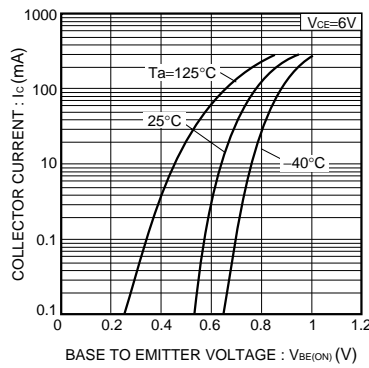


Fig.2 Grounded emitter propagation characteristics (II)

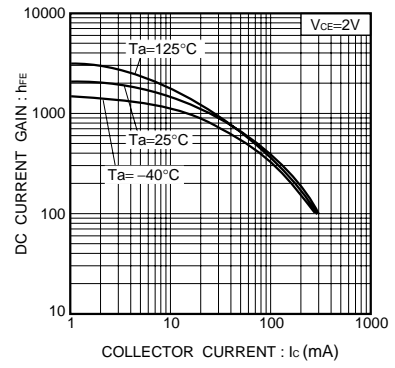


Fig.3 DC current gain vs. collector current (I)

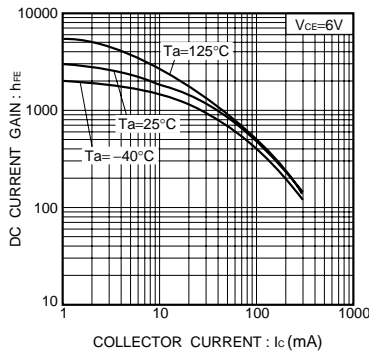


Fig.4 DC current gain vs. collector current (II)

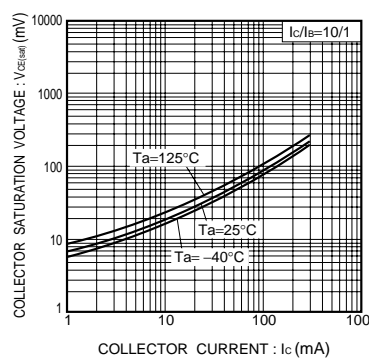


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

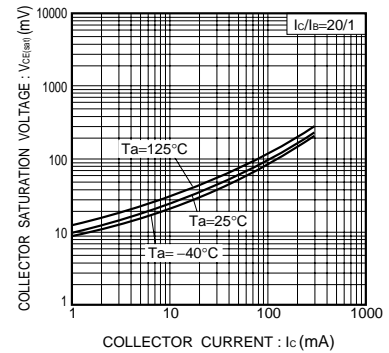


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

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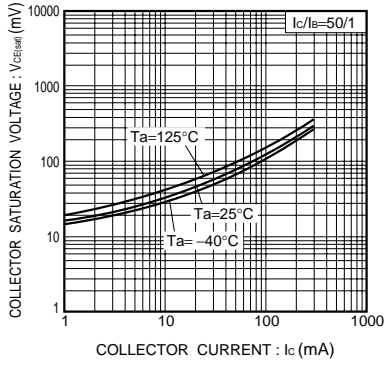


Fig.7 Collector-emitter saturation voltage vs. collector current (III)

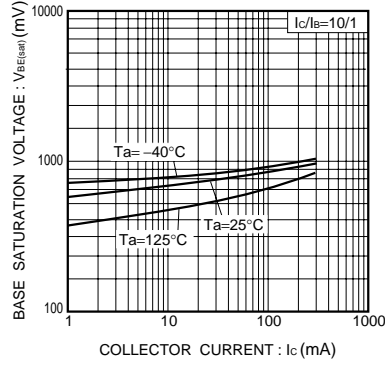


Fig.8 Base-emitter saturation voltage vs. collector current (I)

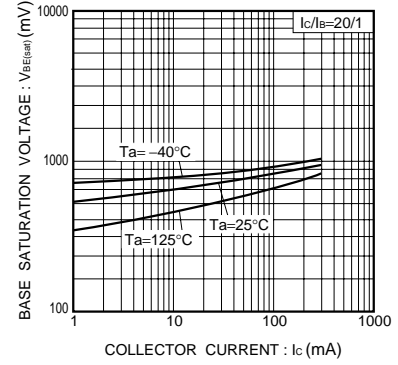


Fig.9 Base-emitter saturation voltage vs. collector current (II)

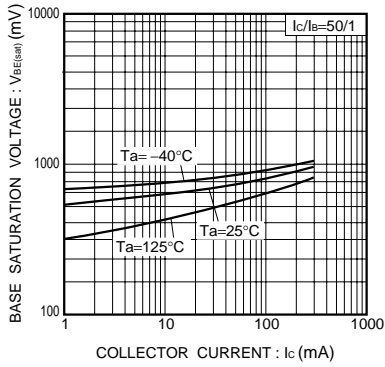


Fig.10 Base-emitter saturation voltage vs. collector current (III)

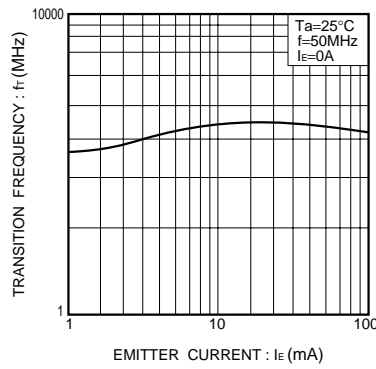


Fig.11 Gain bandwidth product vs. emitter current

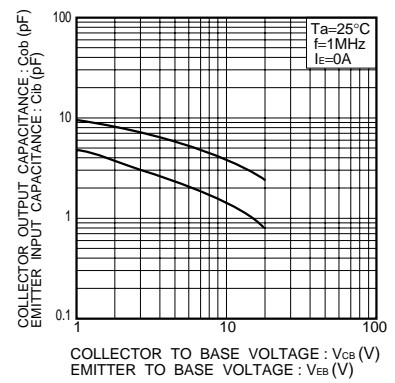


Fig.12 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

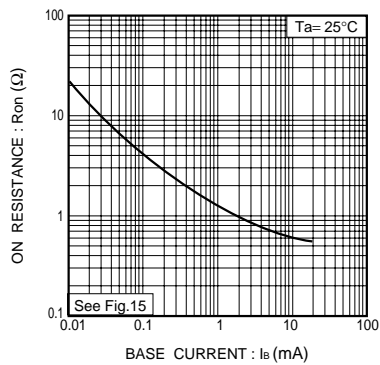


Fig.13 Output-on resistance vs. base current (I)

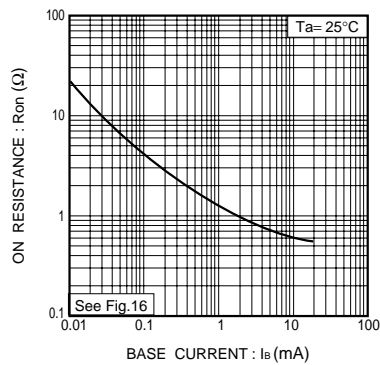


Fig.14 Output-on resistance vs. base current (II)

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●Ron measurement circuit

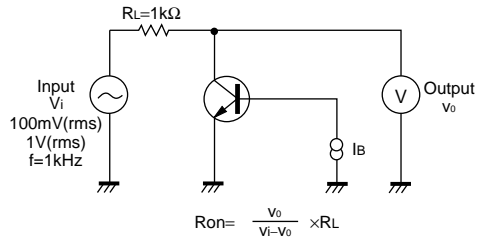


Fig.15 Ron measurement circuit (I)

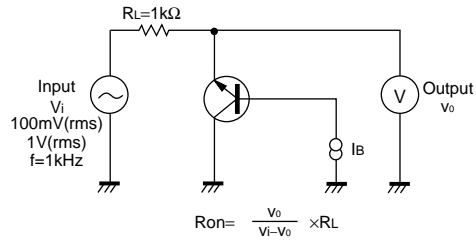


Fig.16 Ron measurement circuit (II)

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